

30V, N-Channel NexFET™ Power MOSFETs

Check for Samples: [CSD17301Q5A](#)

FEATURES

- Optimized for 5V Gate Drive
- Ultralow Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

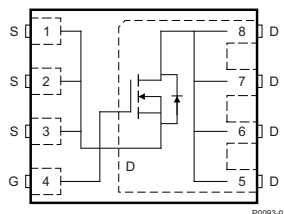
APPLICATIONS

- Notebook Point of Load
- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

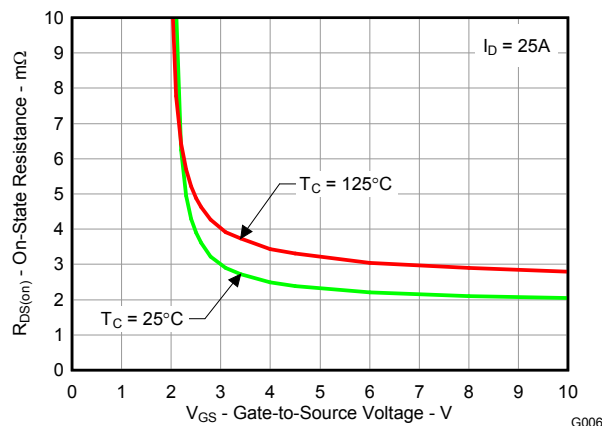
DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications, and optimized for 5V gate drive applications.

Top View



P0093-01

 $R_{DS(on)}$ vs V_{GS}


G006

PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	30	V
Q_g	Gate Charge Total (4.5V)	19	nC
Q_{gd}	Gate Charge Gate to Drain	4.3	nC
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 3V$	2.9 mΩ
		$V_{GS} = 4.5V$	2.3 mΩ
		$V_{GS} = 8V$	2 mΩ
$V_{GS(th)}$	Threshold Voltage	1.1	V

ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD17301Q5A	SON 5-mm × 6-mm Plastic Package	13-inch reel	2500	Tape and Reel

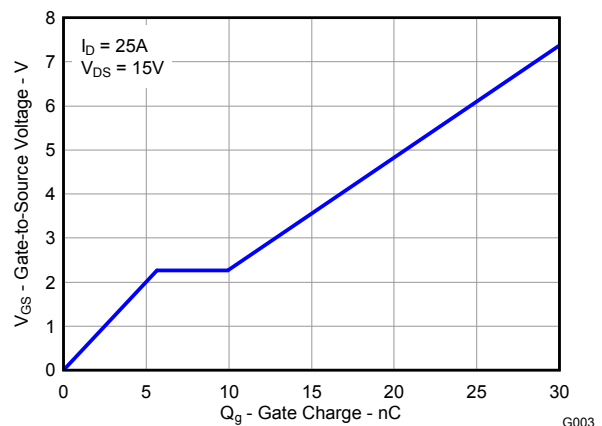
ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	+10 / -8	V
I_D	Continuous Drain Current, $T_C = 25^\circ\text{C}$	100	A
	Continuous Drain Current ⁽¹⁾	28	A
I_{DM}	Pulsed Drain Current, $T_A = 25^\circ\text{C}$ ⁽²⁾	181	A
P_D	Power Dissipation ⁽¹⁾	3.2	W
T_J , T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AS}	Avalanche Energy, single pulse $I_D = 91\text{A}$, $L = 0.1\text{mH}$, $R_G = 25\Omega$	414	mJ

(1) Typical $R_{\theta JA} = 39^\circ\text{C/W}$ on 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Pulse duration $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

GATE CHARGE



G003



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

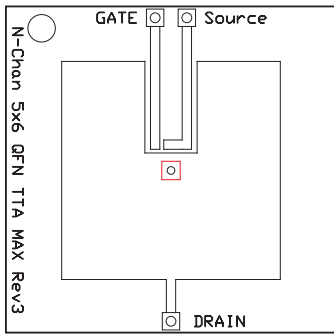
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV _{DSS}	Drain to Source Voltage	V _{GS} = 0V, I _D = 250μA	30			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 24V			1	μA
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = +10 / -8V			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	0.9	1.1	1.55	V
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 3V, I _D = 25A		2.9	3.7	mΩ
		V _{GS} = 4.5V, I _D = 25A		2.3	3	mΩ
		V _{GS} = 8V, I _D = 25A		2	2.6	mΩ
g _{fs}	Transconductance	V _{DS} = 15V, I _D = 25A		149		S
Dynamic Characteristics						
C _{iSS}	Input Capacitance	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		2660	3480	pF
C _{oSS}	Output Capacitance			1420	1850	pF
C _{rSS}	Reverse Transfer Capacitance			80	105	pF
R _G	Series Gate Resistance			1.3	2.6	Ω
Q _g	Gate Charge Total (4.5V)	V _{DS} = 15V, I _D = 25A		19	25	nC
Q _{gd}	Gate Charge Gate to Drain			4.3		nC
Q _{gs}	Gate Charge Gate to Source			5.7		nC
Q _{g(th)}	Gate Charge at V _{th}			2.9		nC
Q _{oss}	Output Charge	V _{DS} = 14V, V _{GS} = 0V		35		nC
t _{d(on)}	Turn On Delay Time	V _{DS} = 15V, V _{GS} = 4.5V, I _D = 25A, R _G = 2Ω		10.7		ns
t _r	Rise Time			16.2		ns
t _{d(off)}	Turn Off Delay Time			28		ns
t _f	Fall Time			10.5		ns
Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _{SD} = 25A, V _{GS} = 0V		0.8	1	V
Q _{rr}	Reverse Recovery Charge	V _{DD} = 14V, I _F = 25A, di/dt = 300A/μs		50		nC
t _{rr}	Reverse Recovery Time			33		ns

THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

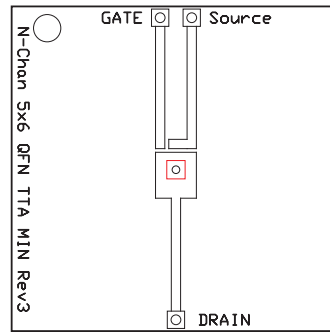
PARAMETER		MIN	TYP	MAX	UNIT
R _{θJC}	Thermal Resistance Junction to Case ⁽¹⁾			2.2	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			49	°C/W

- (1) R_{θJC} is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.



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Max $R_{\theta JA} = 49^{\circ}\text{C/W}$
when mounted on
 1inch^2 of 2 oz. Cu.

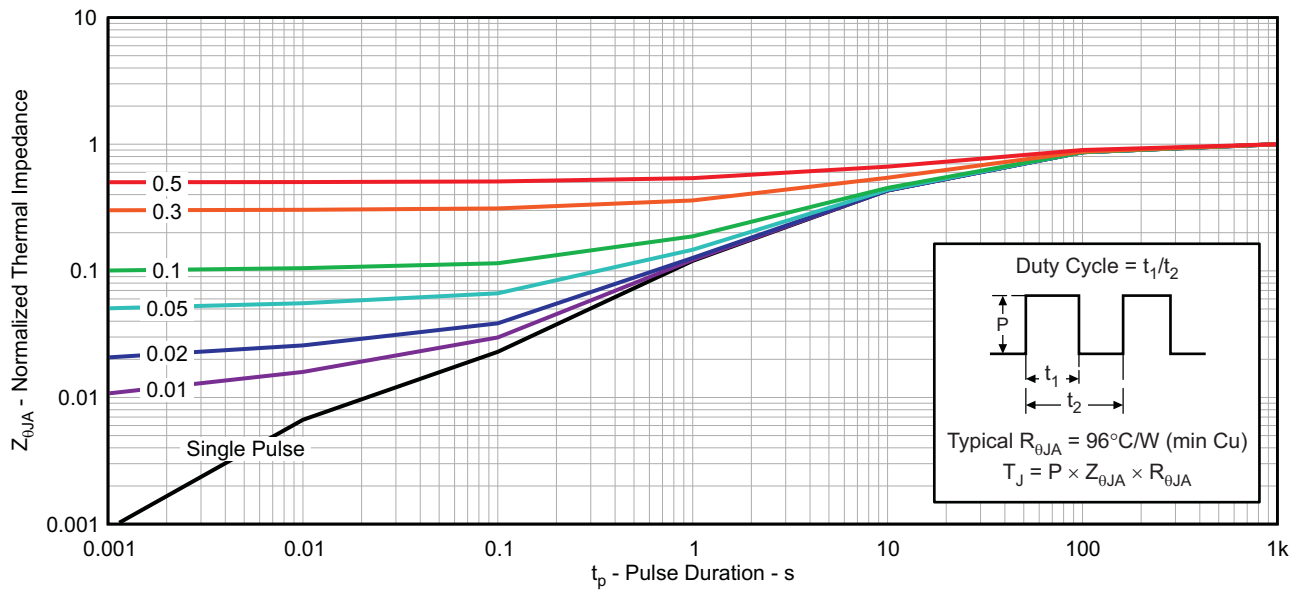


M0137-02

Max $R_{\theta JA} = 120^{\circ}\text{C/W}$
when mounted on
minimum pad area of 2
oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

($T_A = 25^{\circ}\text{C}$ unless otherwise stated)



G012

Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

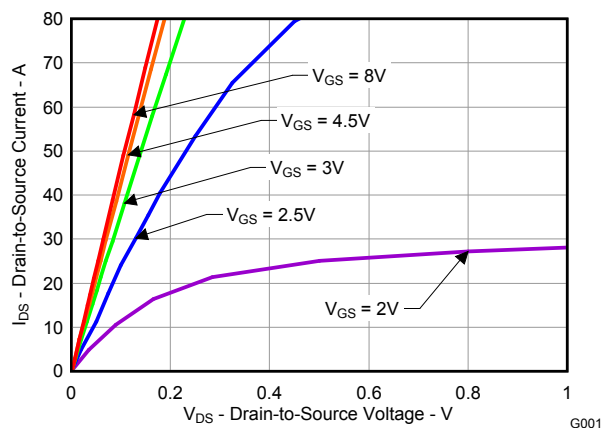


Figure 2. Saturation Characteristics

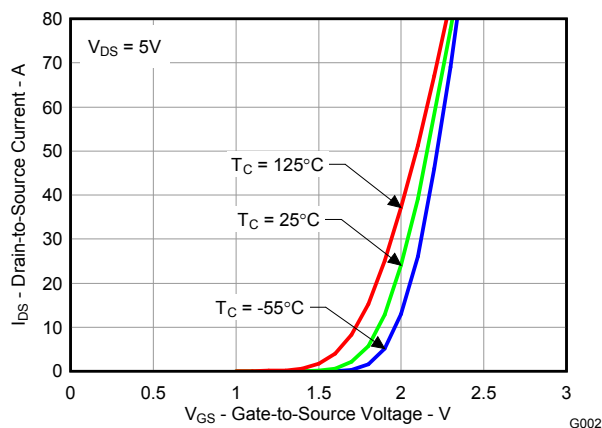


Figure 3. Transfer Characteristics

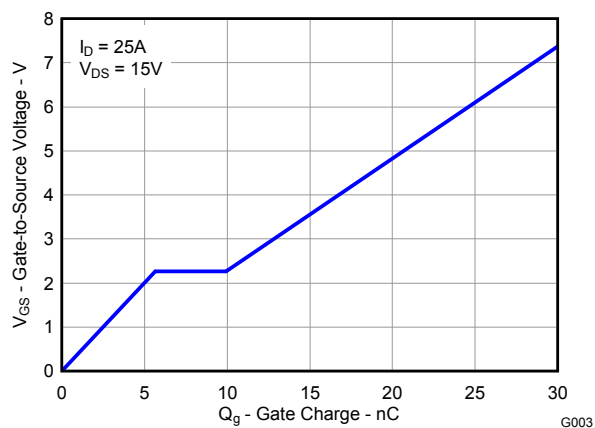


Figure 4. Gate Charge

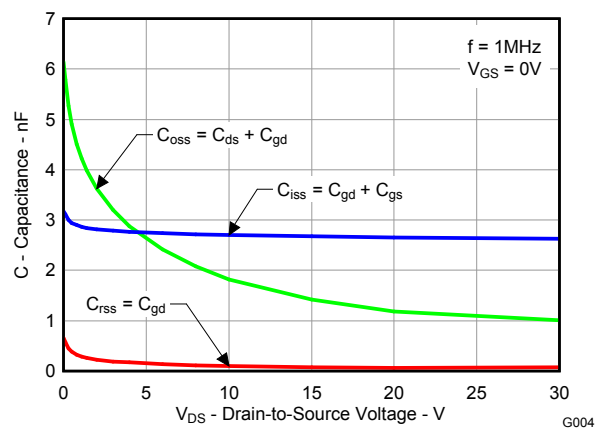


Figure 5. Capacitance

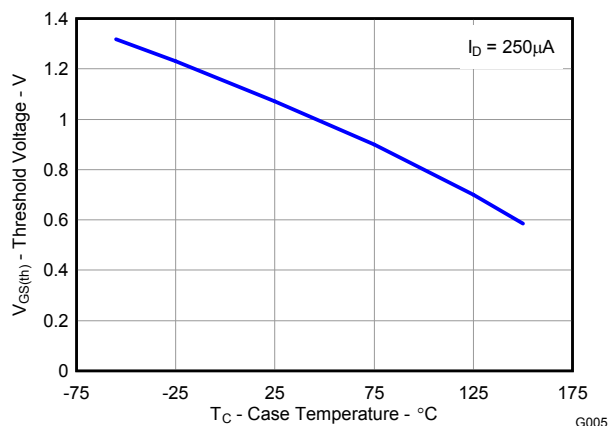


Figure 6. Threshold Voltage vs. Temperature

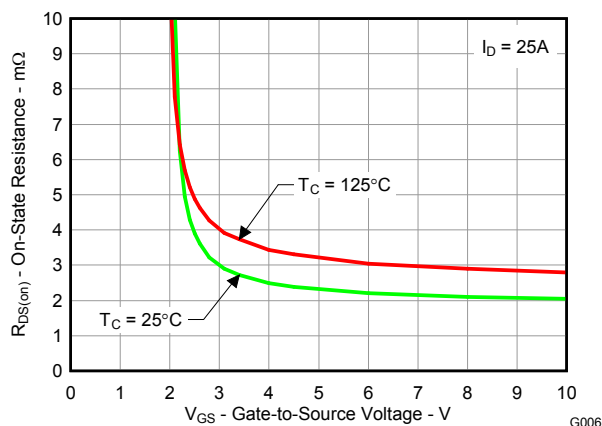


Figure 7. On Resistance vs. Gate Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

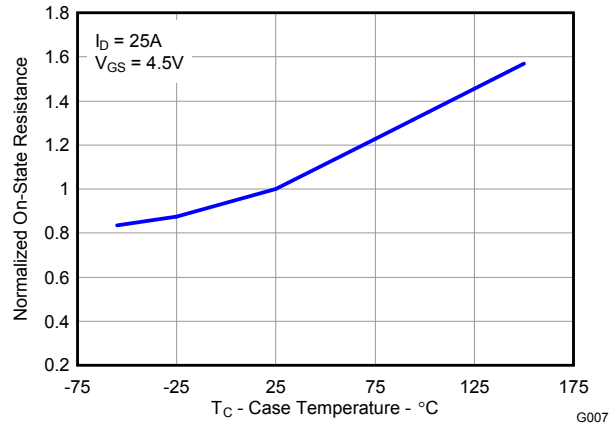


Figure 8. On Resistance vs. Temperature

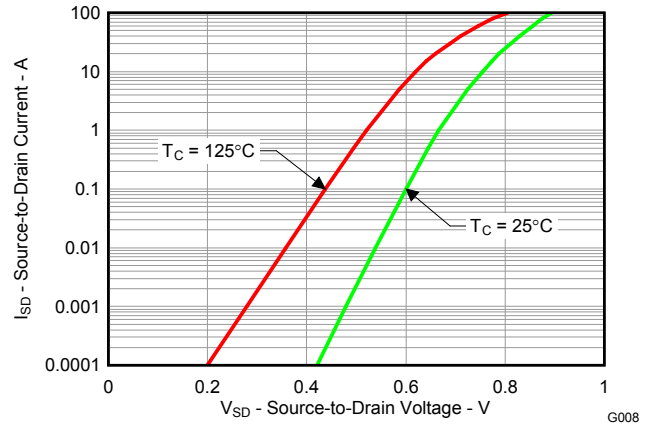


Figure 9. Typical Diode Forward Voltage

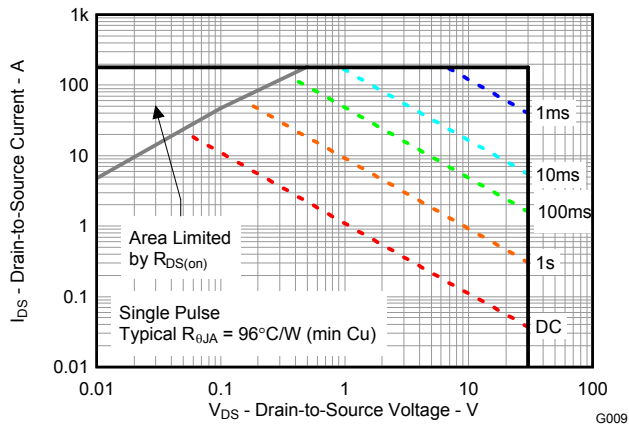


Figure 10. Maximum Safe Operating Area

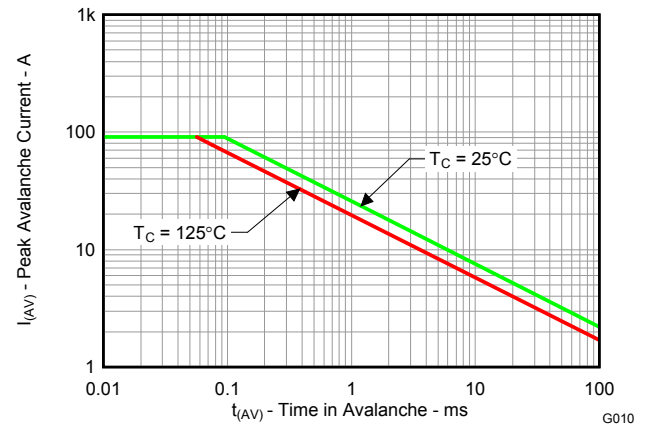


Figure 11. Single Pulse Unclamped Inductive Switching

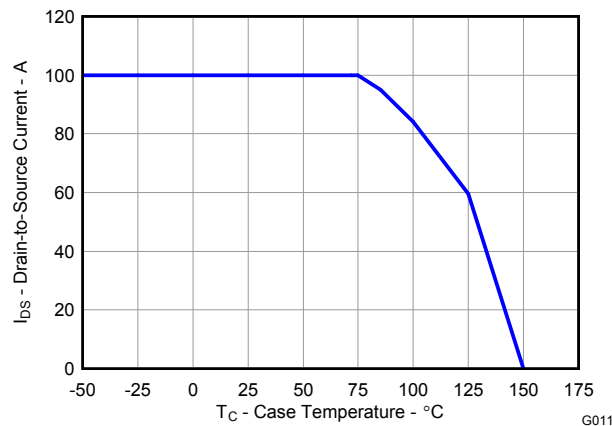
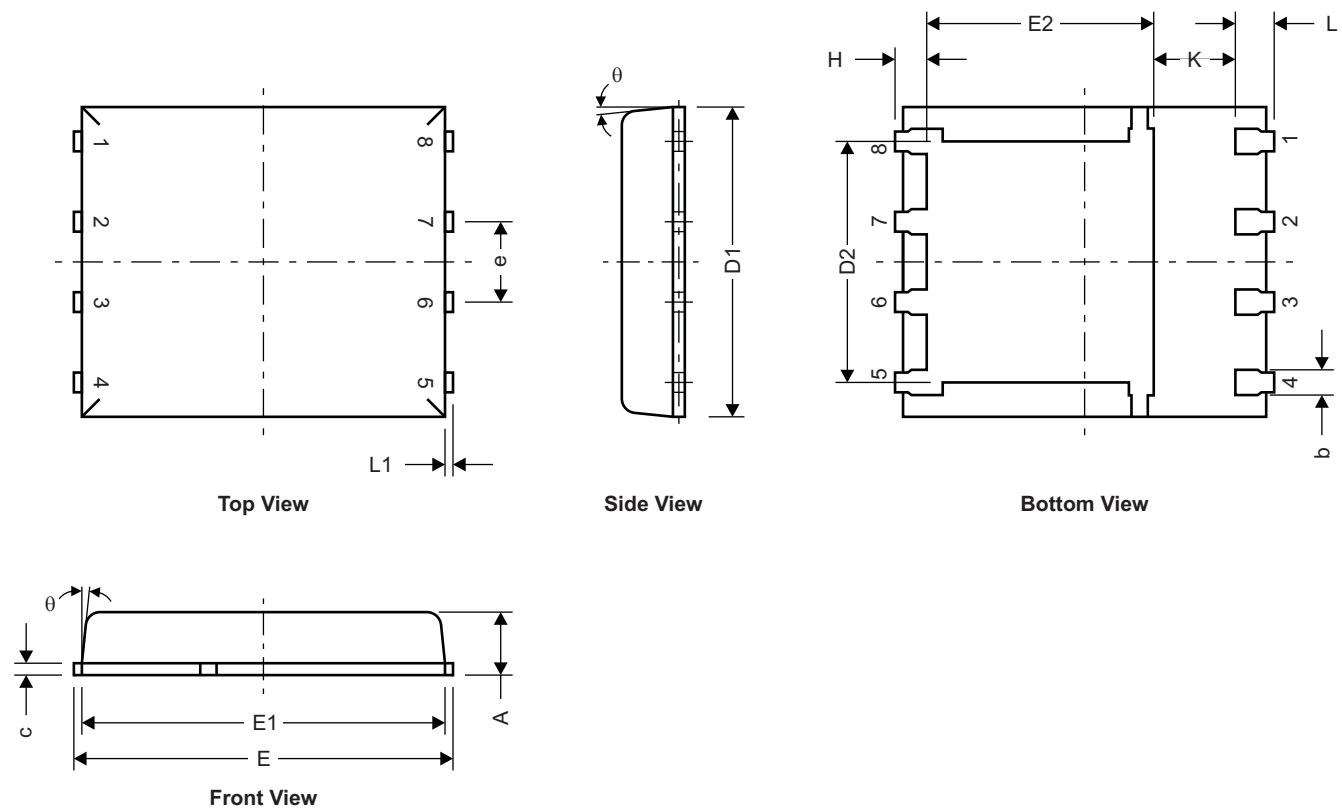


Figure 12. Maximum Drain Current vs. Temperature

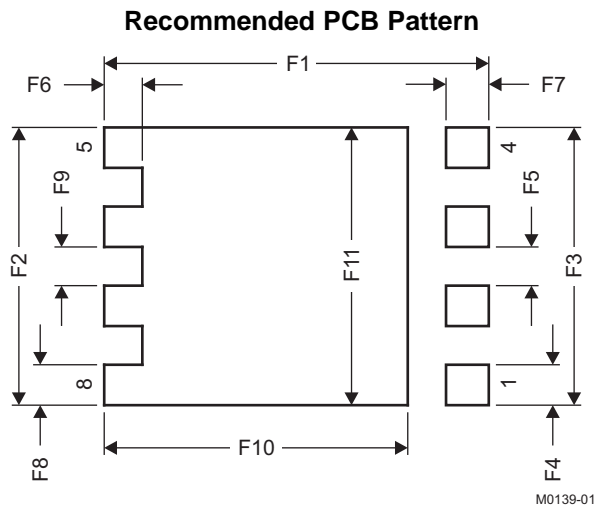
MECHANICAL DATA

Q5A Package Dimensions



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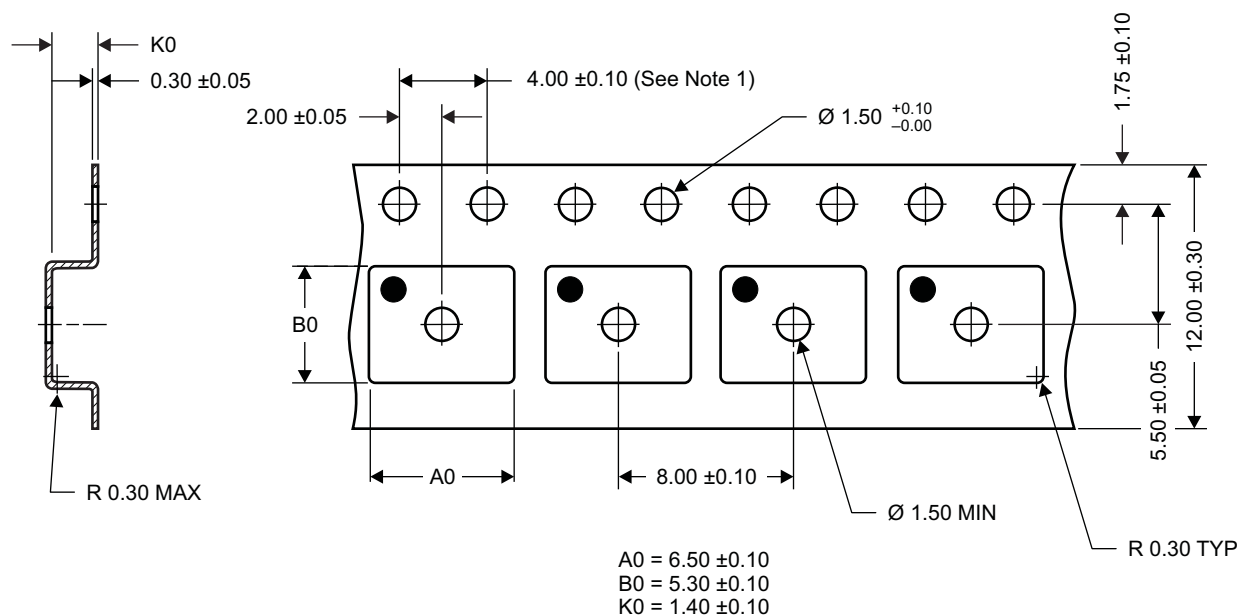
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.33	0.41	0.51
c	0.20	0.25	0.34
D1	4.80	4.90	5.00
D2	3.61	3.81	4.02
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.17	1.27	1.37
H	0.41	0.56	0.71
K	1.10		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°		12°



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note [SLPA005](#) – *Reducing Ringing Through PCB Layout Techniques*.

Q5A Tape and Reel Information



Notes:

- 10-sprocket hole-pitch cumulative tolerance ±0.2
- Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- Material: black static-dissipative polystyrene
- All dimensions are in mm (unless otherwise specified)
- A0 and B0 measured on a plane 0.3mm above the bottom of the pocket

REVISION HISTORY

Changes from Original (January) to Revision A Page

- Changed the Abs Max Ratings table, Avalanche Energy, single pulse From: $I_D = 85A$, $L = 0.1mH$, $R_G = 25\Omega$ Value = 361 To: $I_D = 91A$, $L = 0.1mH$, $R_G = 25\Omega$ Value = 414 1
- Changed [Figure 11](#) 5

Changes from Revision A (February 2010) to Revision B Page

- Updated the Q5A Package Dimensions table. DIM c MAX was 0.30, DIM D2 MAX was 3.96, DIM e MIN was blank MAX was blank, DIM H NOM was 0.51 MAX was 0.61 6
- Deleted Note 6 from the Q5A Tape and Reel Information - "MSL1 260°C (IR and convection) PbF reflow compatible" 7
- Deleted the Package Marking Information section 7

Changes from Revision B (July 2010) to Revision C Page

- Changed the Abs Max Ratings table, Pulsed Drain Current value From: 118 To: 181 1

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD17301Q5A	Active	Production	VSONP (DQJ) 8	2500 LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17301
CSD17301Q5A.B	Active	Production	VSONP (DQJ) 8	2500 LARGE T&R	-	SN	Level-1-260C-UNLIM	-55 to 150	CSD17301

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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